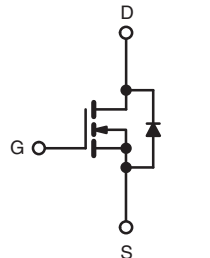
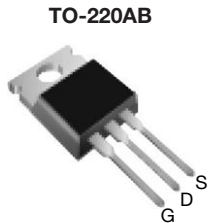


Power MOSFET

PRODUCT SUMMARY		
V_{DS} (V)	500	
$R_{DS(on)}$ (Ω)	$V_{GS} = 10$ V	0.85
Q_g (Max.) (nC)	38	
Q_{gs} (nC)	9.0	
Q_{gd} (nC)	18	
Configuration	Single	



N-Channel MOSFET

FEATURES

- Low Gate Charge Q_g Results in Simple Drive Requirement
- Improved Gate, Avalanche and Dynamic dV/dt Ruggedness
- Fully Characterized Capacitance and Avalanche Voltage and Current
- Effective C_{OSS} Specified
- Compliant to RoHS Directive 2002/95/EC


RoHS*
 COMPLIANT

APPLICATIONS

- Switch Mode Power Supply (SMPS)
- Uninterruptable Power Supply
- High Speed Power Switching

TYPICAL SMPS TOPOLOGIES

- Two Transistor Forward
- Half Bridge
- Full Bridge

ORDERING INFORMATION	
Package	TO-220AB
Lead (Pb)-free	IRF840APbF SiHF840A-E3
SnPb	IRF840A SiHF840A


ABSOLUTE MAXIMUM RATINGS ($T_C = 25$ °C, unless otherwise noted)				
PARAMETER	SYMBOL	LIMIT	UNIT	
Drain-Source Voltage	V_{DS}	500	V	
Gate-Source Voltage	V_{GS}	± 30		
Continuous Drain Current	V_{GS} at 10 V	$T_C = 25$ °C	8.0	A
		$T_C = 100$ °C	5.1	
Pulsed Drain Current ^a	I_{DM}	32		
Linear Derating Factor		1.0	W/°C	
Single Pulse Avalanche Energy ^b	E_{AS}	510	mJ	
Repetitive Avalanche Current ^a	I_{AR}	8.0	A	
Repetitive Avalanche Energy ^a	E_{AR}	13	mJ	
Maximum Power Dissipation	$T_C = 25$ °C	P_D	125	W
Peak Diode Recovery dV/dt ^c	dV/dt	5.0	V/ns	
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to + 150	°C	
Soldering Recommendations (Peak Temperature)	for 10 s	300 ^d		
Mounting Torque	6-32 or M3 screw		10	lbf · in
			1.1	N · m

Notes

- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- $V_{DD} = 50$ V, starting $T_J = 25$ °C, $L = 16$ mH, $R_g = 25$ Ω , $I_{AS} = 8.0$ A (see fig. 12).
- $I_{SD} \leq 8.0$ A, $dI/dt \leq 100$ A/ μ s, $V_{DD} \leq V_{DS}$, $T_J \leq 150$ °C.
- 1.6 mm from case.

* Pb containing terminations are not RoHS compliant, exemptions may apply

THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient	R_{thJA}	-	62	°C/W
Case-to-Sink, Flat, Greased Surface	R_{thCS}	0.50	-	
Maximum Junction-to-Case (Drain)	R_{thJC}	-	1.0	

SPECIFICATIONS ($T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$		500	-	-	V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	Reference to $25\text{ }^\circ\text{C}$, $I_D = 1\text{ mA}$		-	0.58	-	V/°C
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$		2.0	-	4.0	V
Gate-Source Leakage	I_{GSS}	$V_{GS} = \pm 30\text{ V}$		-	-	± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 500\text{ V}, V_{GS} = 0\text{ V}$		-	-	25	μA
		$V_{DS} = 400\text{ V}, V_{GS} = 0\text{ V}, T_J = 125\text{ }^\circ\text{C}$		-	-	250	
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}$	$I_D = 4.8\text{ A}^b$	-	-	0.85	Ω
Forward Transconductance	g_{fs}	$V_{DS} = 50\text{ V}, I_D = 4.8\text{ A}^b$		3.7	-	-	S
Dynamic							
Input Capacitance	C_{iss}	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1.0\text{ MHz}$, see fig. 5		-	1018	-	pF
Output Capacitance	C_{oss}			-	155	-	
Reverse Transfer Capacitance	C_{rss}			-	8.0	-	
Output Capacitance	C_{oss}	$V_{GS} = 0\text{ V}; V_{DS} = 1.0\text{ V}, f = 1.0\text{ MHz}$		-	1490	-	
Output Capacitance	C_{oss}	$V_{GS} = 0\text{ V}; V_{DS} = 400\text{ V}, f = 1.0\text{ MHz}$		-	42	-	
Effective Output Capacitance	$C_{oss\text{ eff.}}$	$V_{GS} = 0\text{ V}; V_{DS} = 0\text{ V to } 400\text{ V}^c$		-	56	-	
Total Gate Charge	Q_g	$V_{GS} = 10\text{ V}$	$I_D = 8\text{ A}, V_{DS} = 400\text{ V}$, see fig. 6 and 13 ^b	-	-	38	nC
Gate-Source Charge	Q_{gs}			-	-	9.0	
Gate-Drain Charge	Q_{gd}			-	-	18	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 250\text{ V}, I_D = 8\text{ A}$ $R_g = 9.1\text{ }\Omega, R_D = 31\text{ }\Omega$, see fig. 10 ^b		-	11	-	ns
Rise Time	t_r			-	23	-	
Turn-Off Delay Time	$t_{d(off)}$			-	26	-	
Fall Time	t_f			-	19	-	
Drain-Source Body Diode Characteristics							
Continuous Source-Drain Diode Current	I_S	MOSFET symbol showing the integral reverse p - n junction diode		-	-	8.0	A
Pulsed Diode Forward Current ^a	I_{SM}			-	-	32	
Body Diode Voltage	V_{SD}	$T_J = 25\text{ }^\circ\text{C}, I_S = 8\text{ A}, V_{GS} = 0\text{ V}^b$		-	-	2.0	V
Body Diode Reverse Recovery Time	t_{rr}	$T_J = 25\text{ }^\circ\text{C}, I_F = 8\text{ A}, di/dt = 100\text{ A}/\mu\text{s}^b$		-	422	633	ns
Body Diode Reverse Recovery Charge	Q_{rr}			-	2.16	3.24	μC
Forward Turn-On Time	t_{on}	Intrinsic turn-on time is negligible (turn-on is dominated by L_S and L_D)					

Notes

- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- Pulse width $\leq 300\text{ }\mu\text{s}$; duty cycle $\leq 2\%$.
- $C_{oss\text{ eff.}}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 % to 80 % V_{DS} .

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

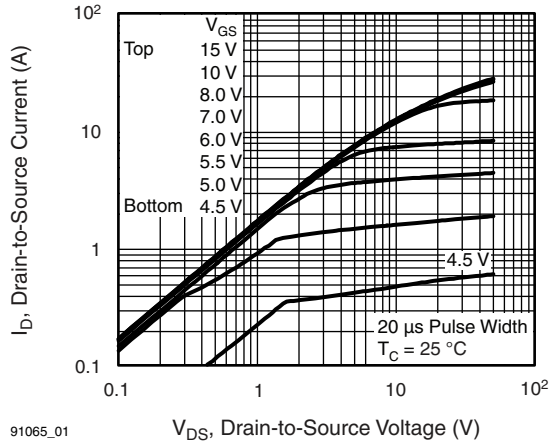


Fig. 1 - Typical Output Characteristics, $T_C = 25\text{ }^\circ\text{C}$

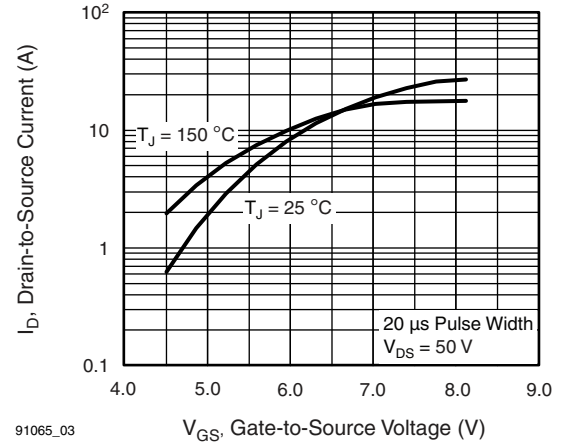


Fig. 3 - Typical Transfer Characteristics

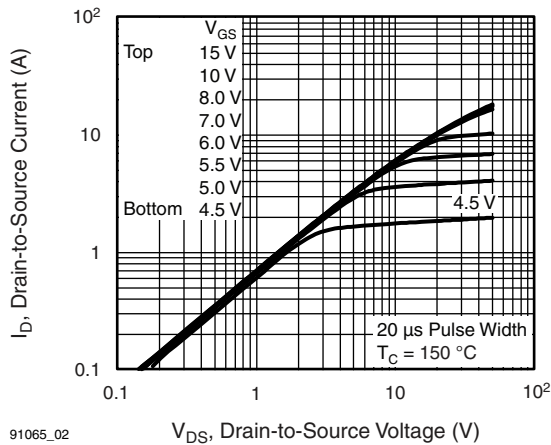


Fig. 2 - Typical Output Characteristics, $T_C = 150\text{ }^\circ\text{C}$

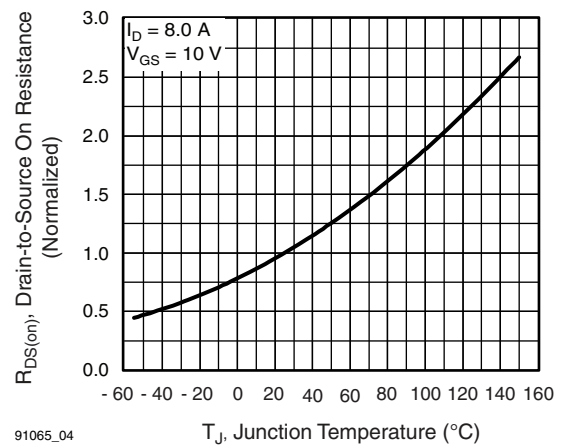
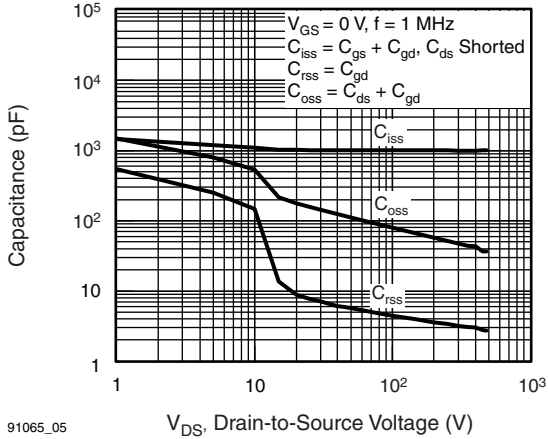
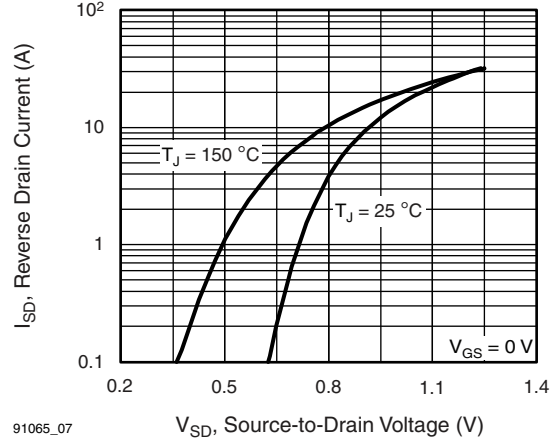


Fig. 4 - Normalized On-Resistance vs. Temperature



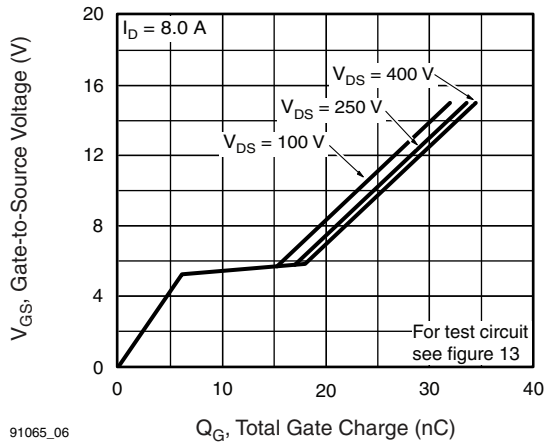
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Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage



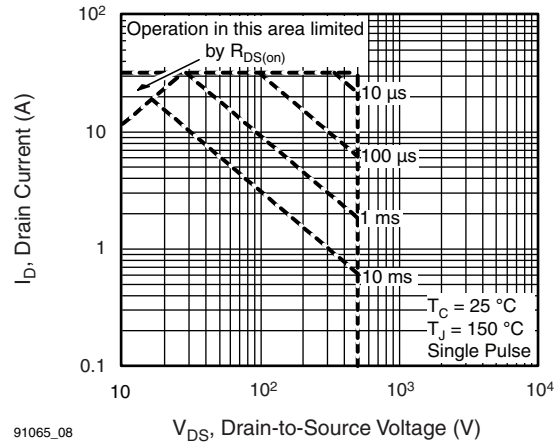
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Fig. 7 - Typical Source-Drain Diode Forward Voltage



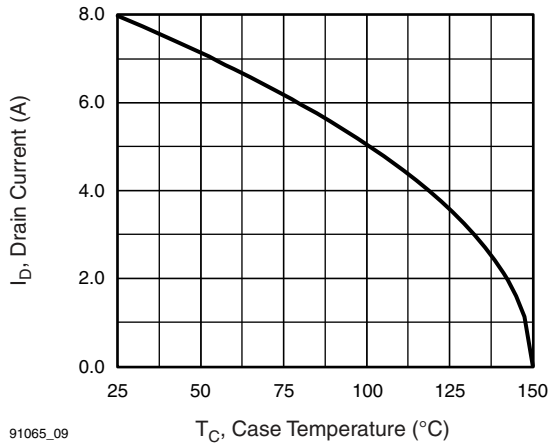
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Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage



91065_08

Fig. 8 - Maximum Safe Operating Area



91065_09

Fig. 9 - Maximum Drain Current vs. Case Temperature

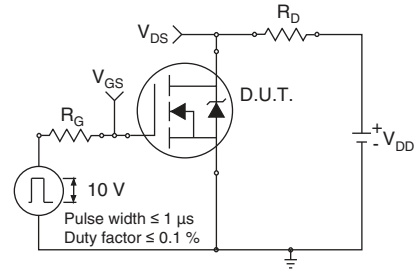
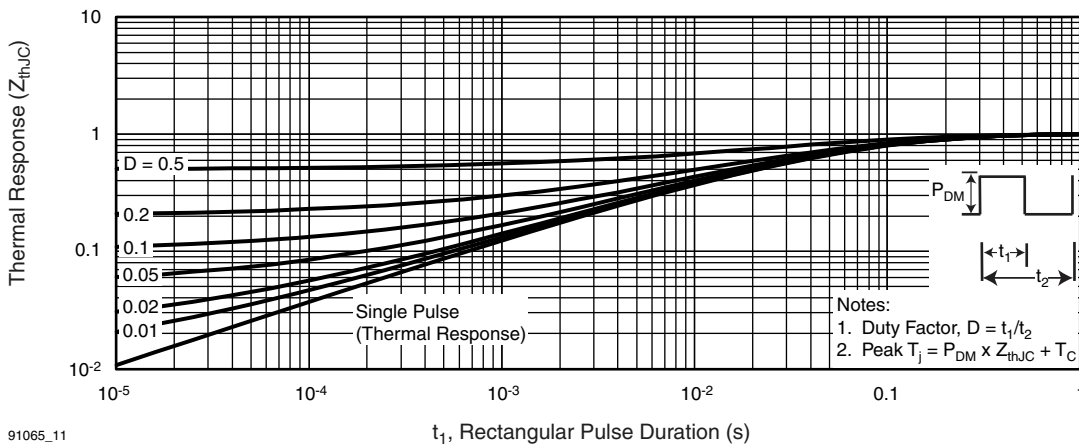


Fig. 10a - Switching Time Test Circuit



Fig. 10b - Switching Time Waveforms



91065_11

Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

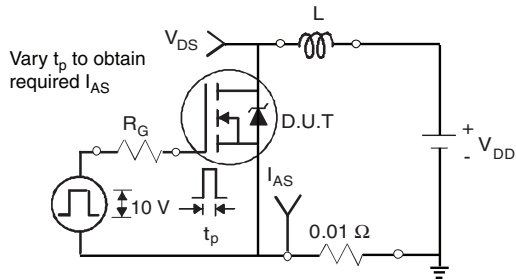


Fig. 12a - Unclamped Inductive Test Circuit

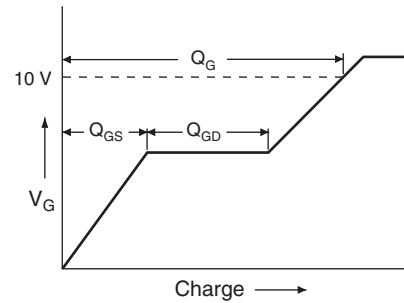


Fig. 12d - Basic Gate Charge Waveform

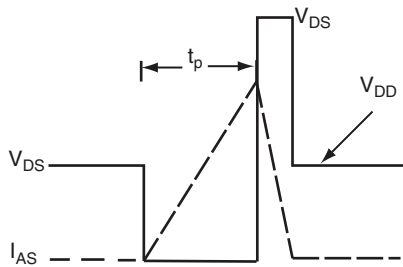


Fig. 12b - Unclamped Inductive Waveforms

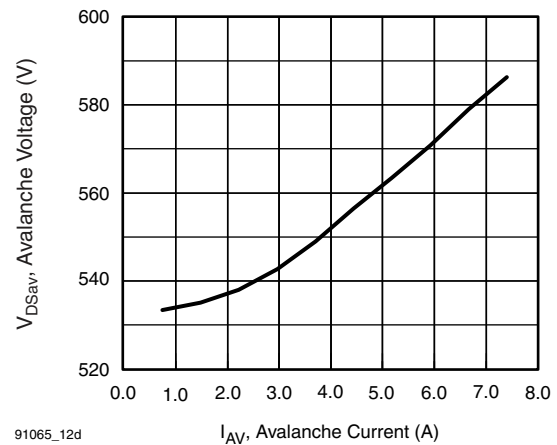


Fig. 13a - Typical Drain-to-Source Voltage vs. Avalanche Current

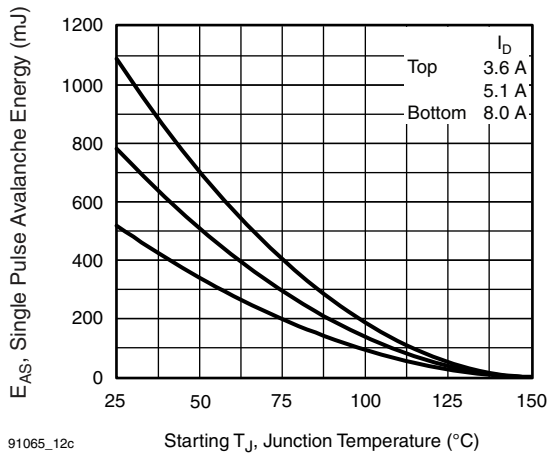


Fig. 12c - Maximum Avalanche Energy vs. Drain Current

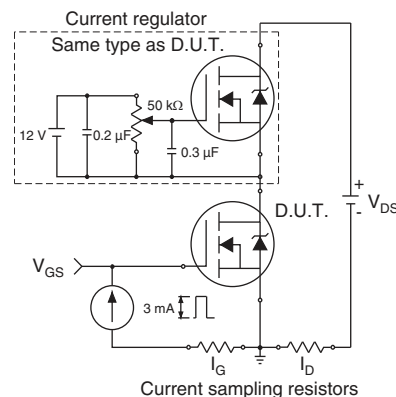


Fig. 13b - Gate Charge Test Circuit

Peak Diode Recovery dV/dt Test Circuit



Note

a. $V_{GS} = 5 V$ for logic level devices

Fig. 14 - For N-Channel

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TO-220-1



DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	4.24	4.65	0.167	0.183
b	0.69	1.02	0.027	0.040
b(1)	1.14	1.78	0.045	0.070
c	0.36	0.61	0.014	0.024
D	14.33	15.85	0.564	0.624
E	9.96	10.52	0.392	0.414
e	2.41	2.67	0.095	0.105
e(1)	4.88	5.28	0.192	0.208
F	1.14	1.40	0.045	0.055
H(1)	6.10	6.71	0.240	0.264
J(1)	2.41	2.92	0.095	0.115
L	13.36	14.40	0.526	0.567
L(1)	3.33	4.04	0.131	0.159
Ø P	3.53	3.94	0.139	0.155
Q	2.54	3.00	0.100	0.118

ECN: X15-0364-Rev. C, 14-Dec-15
DWG: 6031

Note

- M* = 0.052 inches to 0.064 inches (dimension including protrusion), heatsink hole for HVM





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